Lecture 3: Survey of sensing principles

- Sensor classification
- Mechanical sensors
- Thermal sensors
- Chemical sensors



Sensor classification schemes

- Sensors can be classified, among others, according to one of the following criteria
 - Power supply requirements
 - Passive and active
 - Nature of the output signal
 - Digital and analog
 - Measurement operational mode
 - Deflection and null modes
 - Input/output dynamic relationships (covered in Lecture 2)
 - Zero, first, second order, etc.
 - Measurand
 - Mechanical, thermal, magnetic, radiant, chemical
 - Physical measurement variable
 - Resistance, inductance, capacitance, etc.



Passive and active sensors

Passive or self-generating

- Directly generate an electrical signal in response to an external stimuli without the need for an external power supply
 - Output signal power comes from the stimulus
- Examples
 - Thermocouple
 - Piezoelectric sensors

Active or modulating

- These sensors require external power supply or an excitation signal for their operation
 - Output signal power comes from the power supply
- Examples
 - Thermistors
 - Chemo-resistors



Analog and digital sensors

Analog sensors

- Provide a signal that is <u>continuous</u> in both its magnitude and temporal or spatial content
 - Most of the physical measurands are analog in nature
- Examples: Temperature, displacement, light intensity

Digital sensors

- Their output takes the form of <u>discrete</u> steps or states
 - Digital signals are more repeatable, reliable and easier to transmit
- Examples: Shaft encoder, contact switch









Operational modes

Deflection mode

- The sensor or instrument generates a response that is a deflection or a deviation from the initial condition of the instrument
 - The deflection is proportional to the measurand of interest

Null mode

- The sensor or instrument exerts an influence on the measured system so as to oppose the effect of the measurand
 - The influence and measurand are balanced (typically through feedback) until they are equal but opposite in value, yielding a null measurement
- Null mode instrumentation can produce very accurate measurements, but are not as fast as deflection instruments







Mechanical measurands

Displacement

- Resistive sensors
- Capacitive sensors
- Inductive sensors

Force and acceleration

- Strain gauges
- Cantilever beam-based sensors



Resistive displacement sensors

- A resistance with a movable contact (a potentiometer) may be used to measure linear or rotational displacements
 - A known voltage is applied to the resistor ends
 - The contact is attached to the moving object of interest
 - The output voltage at the contact is proportional to the displacement

Notes

- Non-linearities as a result of loading effects
- Resolution due to limited number of turns per unit distance
- Contact wear as a result of frictions





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Capacitive displacement sensors

The capacitance of a parallel plate capacitor is



- d is the separation between the plates, A is the area of the plates, ϵ_0 is the permittivity of air and ϵ_r is the relative permittivity of the dielectric
- A moving object is attached to the dielectric or the plates to generate capacitance changes



Notes

- Variable distance (d) sensors operate over a range of a few millimeters
- Cross-sensitivity to temperature and humidity (specially if the dielectric is air)
- Capacitive sensors are also commonly used to measure pressure
 - "Condenser" microphones measure changes in air pressure of incoming sound waves



Inductive displacement sensors

Linear Variable Differential Transformer (LVDT)

• Motion of a magnetic core changes the mutual inductance of two secondary coils relative to a primary coil





- Primary coil voltage: V_Ssin(ωt)
- Secondary coil induced emf: $V_1 = k_1 \sin(\omega t + \phi)$ and $V_2 = k_2 \sin(\omega t + \phi)$
 - k₁ and k₂ depend on the amount of coupling between the primary and the secondary coils, which is proportional to the position of the coil
 - When the coil is in the central position, $k_1 = k_2 \Rightarrow V_{OUT} = V_1 V_2 = 0$
 - When the coil is is displaced x units, $k_1 \neq k_2 \Rightarrow V_{OUT} = (k_1 k_2) \sin(\omega t + \phi)$
 - Positive or negative displacements are determined from the phase of V_{OUT}

Inductive displacement sensors (cont)

LVDT Characteristics

- Typical LVDTs run at 5V, 2kHz
- LVDTs can measure from mm down to μm
- Due to small variations in the windings, a small residual voltage appears at the output when the coil is in the central position

Advantages of the LVDT over other displacement sensors

- No mechanical wear ensures a long life
- Complete electrical isolation
- DC versions with integrated oscillators are available



Strain gauges

- Strain gauges are devices whose resistance changes with stress (piezo-resistive effect)
 - Strain is a fractional change (ΔL/L) in the dimensions of an object as a result of mechanical stress (force/area)
 - The resistance R of a strip of material of length L, cross-section A and resistivity ρ is R= ρ L/A
 - Differentiating, the gauge factor G becomes

$$\frac{\Delta R}{R} = \frac{\Delta L}{L} - \frac{\Delta A}{A} + \frac{\Delta \rho}{\rho} \cong (1 + 2v) \frac{\Delta L}{L} + \frac{\Delta \rho}{\rho} \Longrightarrow G = \frac{\Delta R/R}{\Delta L/L} = \underbrace{(1 + 2v)}_{\substack{\text{GEOMETRIC} \\ \text{EFFECT}}} + \underbrace{\frac{\Delta \rho}{\rho \Delta L}}_{\substack{\text{DEZO-RESISTIVE} \\ \text{EFFECT}}}$$

- Where v is the Poisson's ratio (v \cong 0.3), which determines the strain in directions normal to L
 - In metal foil gauges, the geometric term dominates (G≅2)
 - In <u>semiconductor</u> gauges, the piezo-resistive term dominates (G≅100)





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Strain gauges

Fabrication and use

- Typical strain gauges consist of a foil or wire grid covered by two sheets of insulation (polyimide)
- The gauge is attached to the desired object with an adhesive
- Longitudinal segments are aligned with the direction of stress
- Sensitivity to traverse stress can be neglected



From [BW96]

Notes

- Temperature effects are quite pronounced in semiconductor gauges
 - To compensate it is common to place "dummy" gauges that are subject to the same temperature changes but no mechanical stress
- Resistance changes are typically very small
 - Strain gauges are almost invariable used in a Wheatstone bridge (to be covered in lectures 4-6)



Force and acceleration sensors

Force sensors

- The coupled-double-beam load cell
 - Dumb-bell cut-out provides areas of maximum strain for the gauges
 - Cantilever beam bends in an S-shape
 - This induces both compressive and tensile strains that can be easily measured in a bridge arrangement



Acceleration sensors

- Spring-mass-damper accelerometer
 - Covered in the previous lecture
- Cantilever-beam with strain gauges
 - A seismic mass is attached to the end of the cantilever
 - Dampening is usually performed with viscous fluids or permanent magnets





Temperature sensors

Thermoresistive sensors

- Resistive Temperature Devices (RTD)
- Thermistors

Thermoelectric sensors

- The Seebeck effect
- The Peltier effect
- Thermocouples

p-n junction sensors

• Covered in the Lab



Thermoresistive sensors

- Based on materials whose resistance changes in accordance with temperature
 - Resistance Temperature Detectors (RTDs)
 - The material is a metal
 - Platinum, Nickel, Copper are typically used
 - Positive temperature coefficients

$$R_{_{T}} = R_{_{0}} \Big[1 + \alpha_{_{1}}T + \alpha_{_{2}}T^{_{2}} + \cdots + \alpha_{_{n}}T^{_{n}} + \Big] \cong R_{_{0}} \Big[1 + \alpha_{_{1}}T \Big]$$

- Thermistors ("thermally sensitive resistor")
 - The material is a semiconductor
 - A composite of a ceramic and a metallic oxide (Mn, Co, Cu or Fe)
 - Typically have negative temperature coefficients (NTC thermistors)

$$R_{T} = R_{0} exp \left[B \left(\frac{1}{T} - \frac{1}{T_{0}} \right) \right]$$



Thermoelectric sensors

The Seebeck effect

• When a pair of dissimilar metals are joined at one end, and there is a temperature difference between the joined ends and the open ends, thermal emf is generated, which can be measured in the open ends

The Peltier effect

• When a current passes through the junction of two different conductors, heat can be either absorbed or released depending on the direction of current flow

Thermocouples

- Based on the Seebeck effect
- Open ends must be kept at a constant reference temperature T_{REF}
- A number of standard TCs are used
 - These are denominated with different letter codes: T, J, K, S, R...
 - i..e, type J (the most popular) is made of Iron and Constantan (Cu/Ni alloy: 57/43)





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RTDs vs. thermocouples vs. IC sensors

| | THERMOCOUPLES | RTD | IC |
|-------------|--|-----------------------------------|--------------------|
| ACCURACY | Limits of error wider than RTD or IC Sensor | Better accuracy than thermocouple | Best accuracy |
| RUGGEDNESS | Excellent | Sensitive to strain and shock | Sensitive to shock |
| TEMPERATURE | -400 to 4200° F | -200 to 1475° F | -70 to 300° F |
| DRIFT | Higher than RTD | Lower than TC | |
| LINEARITY | Very non-linear | Slightly non-linear | Very linear |
| RESPONSE | Fast dependent on size | Slow due to thermal mass | Faster than RTD |
| COST | Rather inexpensive except for noble metals TCs, which are very expensive | More expensive | Low cost |

from http://www.wici.com/technote/table2.htm



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Chemical sensors

Conductivity

- Metal-oxides
- Conducting polymers

Piezo-electric

- Surface Acoustic Wave
- Quartz Crystal Microbalance



Conductivity sensors

Absorption of gases modifies the conductivity of sensing layer

Sensing layer types

- Metal Oxide
 - Typically SnO₂ doped with Pt or Pd
 - Operate a high temperatures (300-500°C)
 - Temperature-selectivity dependency
 - Broad selectivity
 - Particularly suitable for combustible gases
- Conducting Polymers
 - Based on pyrrole, aniline or thiophene
 - Operate at room temperature

CPs vs MOXs

- CP advantages
 - Large number of polymers available with various selectivities
 - Sensitivity* to wide number of VOCs
 - Low power consumption
 - Faster response and recovery times
- CP Limitations
 - Cross-sensitivity* to humidity
 - Lower sensitivity* than MOXs

*By sensitivity here we mean the ability to detect certain VOCs, not the slope of the calibration curve





Piezo-electric chemical sensors

Piezo-electric effect

- The generation of an electric charge by a crystalline material upon subjecting it to stress (or the opposite)
 - A typical piezo-electric material is Quartz (SiO₂)
- Piezo-electric sensors
 - Thin, rubbery polymer layer on a piezo-electric substrate
 - Sensing principle: mass and viscosity changes in the sensing membrane with sorption of VOCs

Surface Acoustic Wave (SAW)

- AC signal (30-300MHz) applied to interdigitated input electrode generates a surface (Rayleigh) wave
- Propagation delays to output electrode are affected by changes in the surface properties
- Phase shifts of the output electrode signal are used as a response

Quartz Crystal Microbalance (QMB)

- Also known as Bulk Acoustic Wave (BAW) devices
- Device is operated in an oscillator circuit
- Changes in the sensing membrane affect the resonant frequency (5-20MHz) of the device





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